Docket No. 243339US3/phh

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukihiko NAKATA, et al.

SERIAL NO: 10/673,173 GAU: 1753

FILED: September 30, 2003 EXAMINER:

FOR: SUBSTRATE PROCESSING APPARATUS AND SUBSTRATE PROCESSING METHOD

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:
Applicant(s) wish to disclose the following information.

REFERENCES

■ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

■ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Joseph A. Scafetta Jr.

C. Irvin McClelland
Registration No. 21,124
Joseph A. Scafetta, Jr.
Registration No. 26,803

Customer Number
22850
Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 05/03)

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STATEMENT OF RELEVANCY

References AV through AY on Form 1449 are discussed in the specification.

Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 243339US3	SERIAL NO. 10/673,173
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Yukihiko NAKATA, et al.	
		FILING DATE September 30, 2003	GROUP 1753

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AV	Y. NAKATA, et al., Proceedings of Int. Conf. on Rapid Thermal Proceeding for Future Semiconductor Device, 2 pages, "RAPID LOW TEMPERATURE PHOTO OXIDATION PROCESSING FOR ADVANCED POLY-Si TFTS", 2001
	AW	Y. NAKATA, et al., Extended Abstracts of International Workshop on Gate Insulator, pages 120-123, "PHOTO OXIDATION AND PECVD STACKED GATE INSULATOR FOR POLY-Si TFTS AT 200-300 °C", November 1-2, 2001
	AX	Y. NAKATA, et al., Asia Display/IDW '01, pages 375-378, "LOW TEMPERATURE GATE INSULATOR FOR POLY-Si TFTS BY COMBINATION OF PHOTO OXIDATION AND PECVD", October 16-19, 2001
	AY	Y. NAKATA, et al., Spring 48th Applied Physics Related Joint Lecture Meeting, page 89, "LOW TEMPERATURE OXIDE FORMATION FOR POLY-Si TFT BY PLASMA AND LIGHT PROCESS", 2001
	AZ	Y. NAKATA, et al., IEICE Transactions on Electronics, vol. E85-C, no. 11, pages 1849-1853, "LOW-TEMPERATURE GATE INSULATOR FOR POLY-Si THIN FILM TRANSISTORS BY COMBINATION OF PHOTO-OXIDATION AND PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION USING TETRAETHYLORTHOSILICATE AND O_2 GASES", November 2002
		☐ Additional References sheet(s) attached	

Examiner	Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.